

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Roger W. WHATMORE, Eijo KOMURO

Application No.: US National Stage of
PCT/GB01/03135

Filed: February 28, 2002

Docket No.: 112113

For: IMPROVEMENTS IN OR RELATING TO FILTERS

PRELIMINARY AMENDMENTDirector of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 1, between lines 1 and 2, insert new paragraphs as follows:

BACKGROUND OF THE INVENTION1. Field of Invention

Page 1, between lines 4 and 5, insert a new paragraph as follows:

2. Description of Related Art

Page 2, between lines 10 and 11, insert a new paragraph as follows:

SUMMARY OF THE INVENTION

Page 4, between lines 16 and 17, insert a new paragraph as follows:

BRIEF DESCRIPTION OF THE DRAWINGS

Page 5, between lines 13 and 14, insert a new paragraph as follows:

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

10/069754-023001

IN THE CLAIMS:

Please replace claims 3-10 as follows:

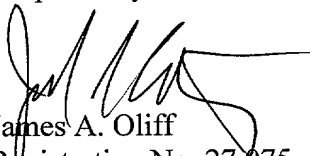
3. (Amended) A method as claimed in claim 1 wherein holes (12;39) are etched and filled with metal (13;40) to allow contacts to be made to the filters (2;28).
4. (Amended) A method as claimed in claim 1 wherein metal layers (44) are deposited on the edges of the filters (28) after they have been separated in order to allow contacts to be made to the filters.
5. (Amended) A method as claimed in claim 1 wherein a third wafer (14;34) is bonded to the first wafer (1;27) on that face remote from the second wafer (8;30).
6. (Amended) A method as claimed in claim 1 wherein one or more of the wafer bonding processes is undertaken under a vacuum.
7. (Amended) A method as claimed in claim 1 wherein one or more of the wafer bonding processes used is anodic bonding employing a borosilicate bonding layer.
8. (Amended) A method as claimed in claim 1 wherein one or more of the wafer bonding processes used employs a low melting point glass as the bonding layer and the bond is made by a combination of heat and pressure.
9. (Amended) A method as claimed in claim 1 wherein one or more of the wafer bonding processes used employs a metal or alloy as the bonding layer and the bond is made by a combination of heat and pressure.
10. (Amended) A filter made by the method according to claim 1.

REMARKS

Claims 1-14 are pending. By this Preliminary Amendment, the specification is amended to conform to U.S. patent practice and claims 3-10 are amended to eliminate multiple dependencies and a typographical error. Prompt and favorable consideration on the merits is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

Respectfully submitted,



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Attached: APPENDIX

Date: February 28, 2002

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| <p>DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461</p> |
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10069754-02200208220-45269001

APPENDIX

Changes to Specification:

Page 1, between lines 1 and 2, new paragraphs are added.

Page 1, between lines 4 and 5, a new paragraph is added.

Page 2, between lines 10 and 11, a new paragraph is added.

Page 4, between lines 16 and 17, a new paragraph is added.

Page 5, between lines 13 and 14, a new paragraph is added.

Changes to Claims:

The following are marked-up versions of the amended claims:

3. (Amended) A method as claimed in claim 1 ~~or claim 2~~ wherein holes (12;39) are etched and filled with metal (13;40) to allow contacts to be made to the filters (2;28).
4. (Amended) A method as claimed in claim 1 ~~or claim 2~~ wherein metal layers (44) are deposited on the edges of the filters (28) after they have been separated in order to allow contacts to be made to the filters.
5. (Amended) A method as claimed in claim 1 ~~any one of the preceding claims~~ wherein a third wafer (14;34) is bonded to the first wafer (1;27) on that face remote from the second wafer (8;30).
6. (Amended) A method as claimed in claim 1 ~~any one of the preceding claims~~ wherein one or more of the wafer bonding processes is undertaken under a vacuum.
7. (Amended) A method as claimed in claim 1 ~~any one of the preceding claims~~ wherein one or more of the wafer bonding processes used is anodic bonding employing a borosilicate bonding layer.
8. (Amended) A method as claimed in claim 1 ~~any one of claims 1 to 6~~ wherein one or more of the wafer bonding processes used employs a low melting point glass as the bonding layer and the bond is made by a combination of heat and pressure.

9. (Amended) A method as claimed in claim 1 ~~any one of claims 1 to 6~~ wherein one or more of the wafer bonding processes used employs a metal or alloy as the bonding layer and the bond is made by a combination of heat and pressure.

10. (Amended) A filter made by the method according to claim 1 ~~any one of the preceding claims~~.